



General Description

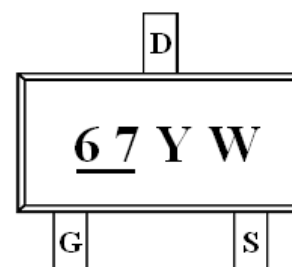
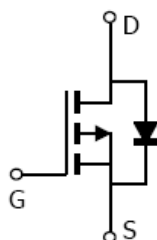
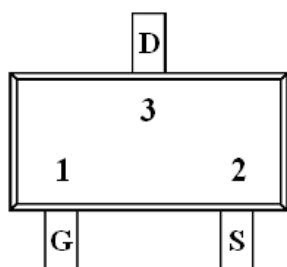
AFP2367AS, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- -20V/-2.8A, $R_{DS(ON)}=80m\Omega@V_{GS}=-4.5V$
- -20V/-2.5A, $R_{DS(ON)}=98m\Omega@V_{GS}=-2.5V$
- -20V/-2.2A, $R_{DS(ON)}=130m\Omega@V_{GS}=-1.8V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

Pin Description (SOT-23)



Application

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Net Working System

Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP2367ASS23RG	6ZYW	SOT-23	Tape & Reel	3000 EA

- ※ 67 parts code
- ※ Y year code (0 ~ 9)
- ※ W week code (A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52)
- ※ AFP2367ASS23RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate –Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current($T_J=150^{\circ}\text{C}$)	I_D	$T_A=25^{\circ}\text{C}$	-3.0
		$T_A=70^{\circ}\text{C}$	-2.2
Pulsed Drain Current	I_{DM}	-10	A
Continuous Source Current(Diode Conduction)	I_S	-1.6	A
Power Dissipation	P_D	$T_A=25^{\circ}\text{C}$	1.25
		$T_A=70^{\circ}\text{C}$	0.8
Operating Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55/150	$^{\circ}\text{C}$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^{\circ}\text{C}/\text{W}$

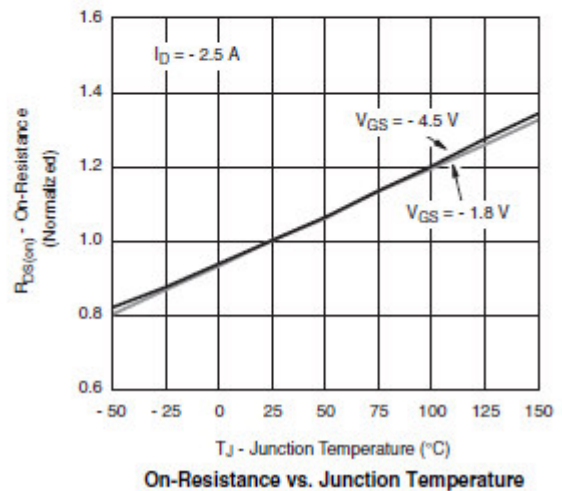
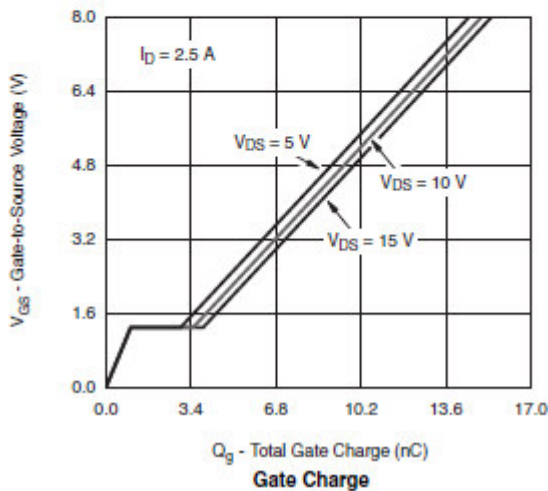
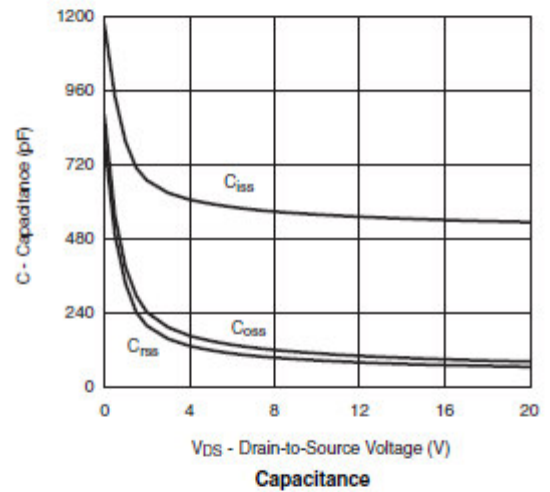
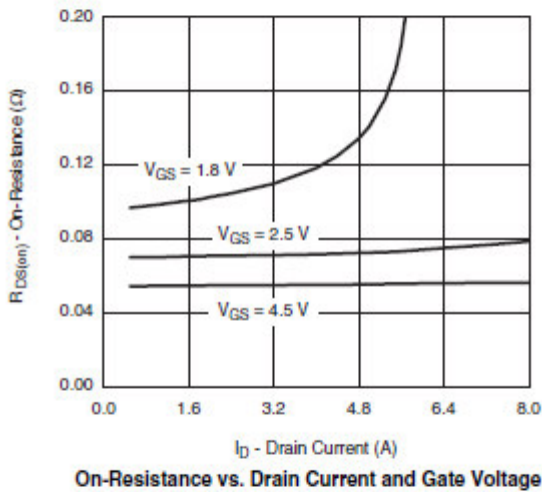
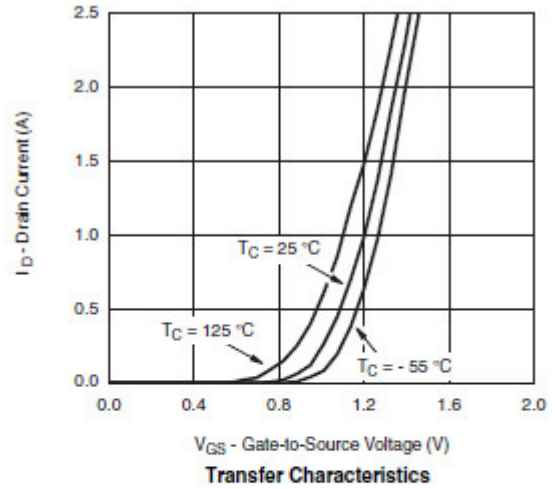
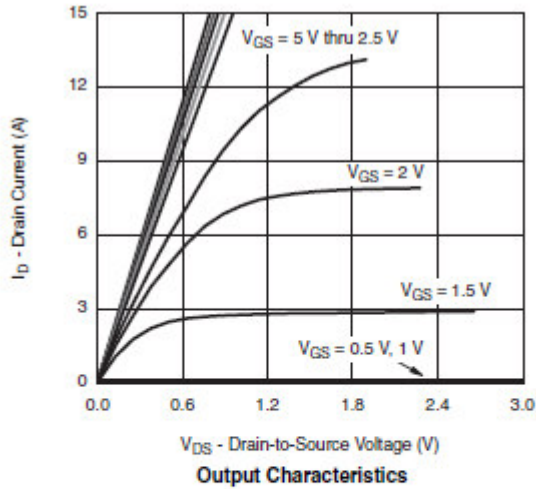
Electrical Characteristics

($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}, I_D=-250\mu\text{A}$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.5		-1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 12\text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-16\text{V}, V_{GS}=0\text{V}$			-1	uA
		$V_{DS}=-16\text{V}, V_{GS}=0\text{V}$ $T_J=85^{\circ}\text{C}$			-30	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5\text{V}, V_{GS}=-4.5\text{V}$	-6			A
		$V_{DS} \leq -5\text{V}, V_{GS}=-2.5\text{V}$	-3			
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5\text{V}, I_D=-2.8\text{A}$		70	80	m Ω
		$V_{GS}=-2.5\text{V}, I_D=-2.5\text{A}$		88	98	
		$V_{GS}=-1.8\text{V}, I_D=-2.2\text{A}$		115	130	
Forward Transconductance	g_{FS}	$V_{DS}=-5\text{V}, I_D=-2.8\text{A}$		6.5		S
Diode Forward Voltage	V_{SD}	$I_S=-1.25\text{A}, V_{GS}=0\text{V}$		-0.75	-1.3	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-6\text{V}, V_{GS}=-4.5\text{V}$ $I_D \equiv -2.8\text{A}$		10	18	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			3.0		
Input Capacitance	C_{iss}	$V_{DS}=-6\text{V}, V_{GS}=0\text{V}$ $f=1\text{MHz}$		450		pF
Output Capacitance	C_{oss}			95		
Reverse Transfer Capacitance	C_{rss}			55		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-6\text{V}, R_L=6\Omega$ $I_D \equiv -1.0\text{A}, V_{GEN}=-4.5\text{V}$ $R_G=6\Omega$		8	18	ns
	t_r			8	18	
Turn-Off Time	$t_{d(off)}$			25	50	
	t_f			25	35	

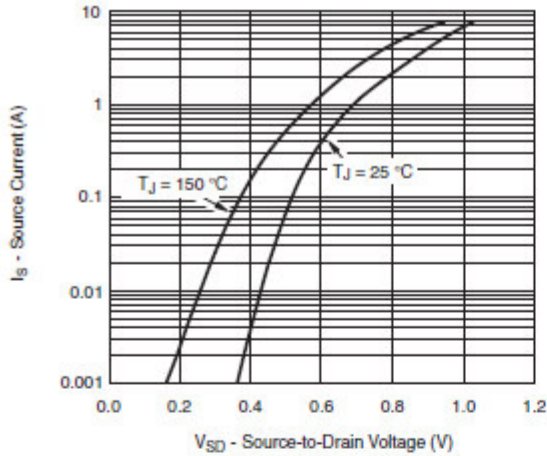


Typical Characteristics

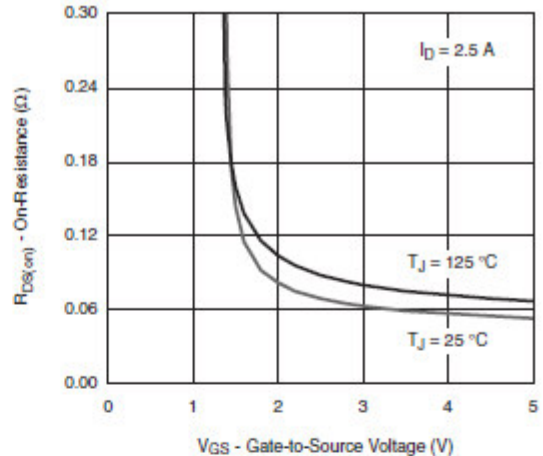




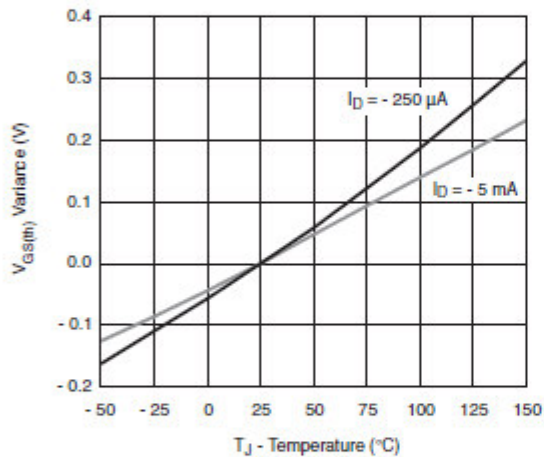
Typical Characteristics



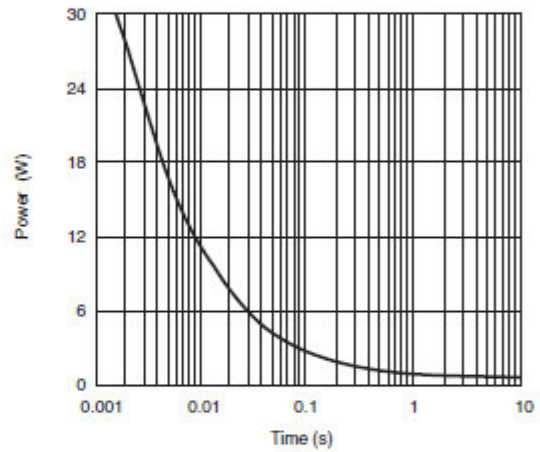
Source-Drain Diode Forward Voltage



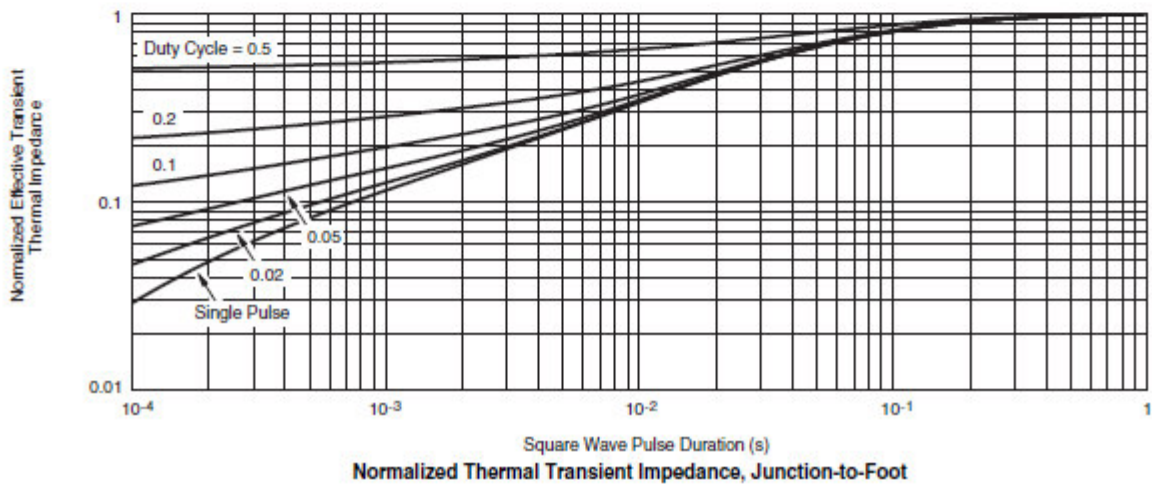
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

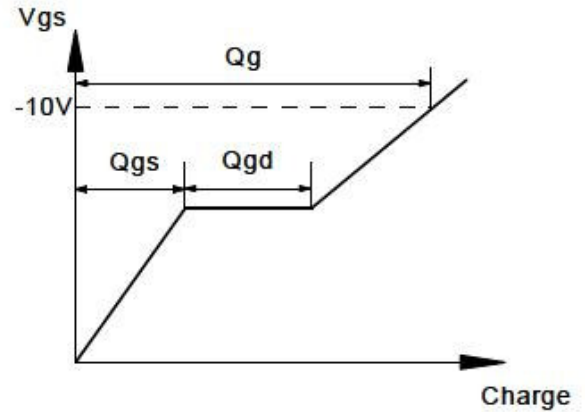
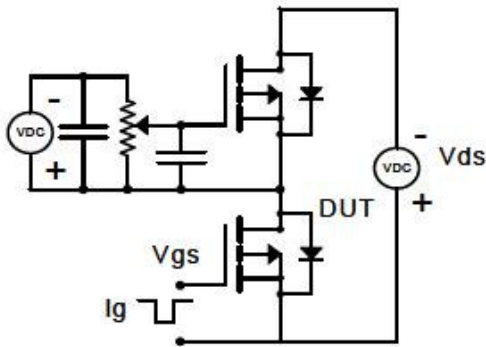


Normalized Thermal Transient Impedance, Junction-to-Foot

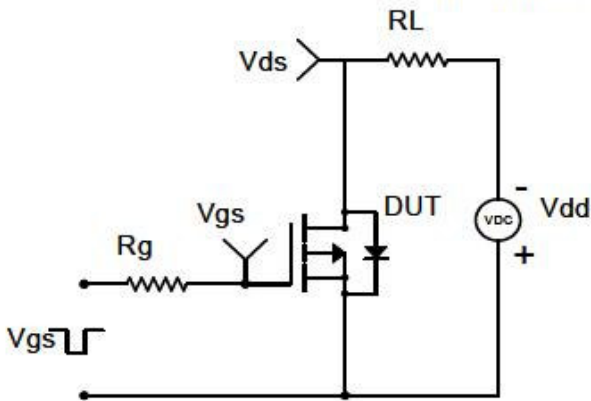


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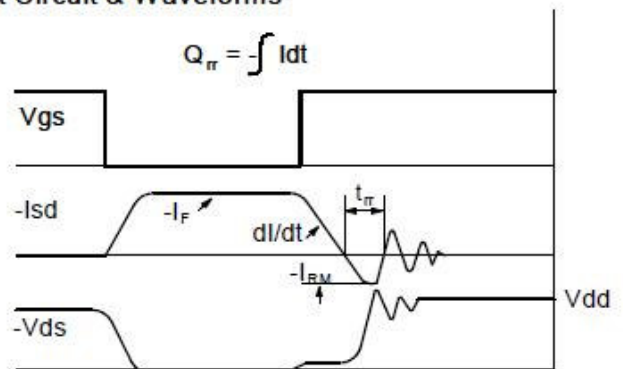
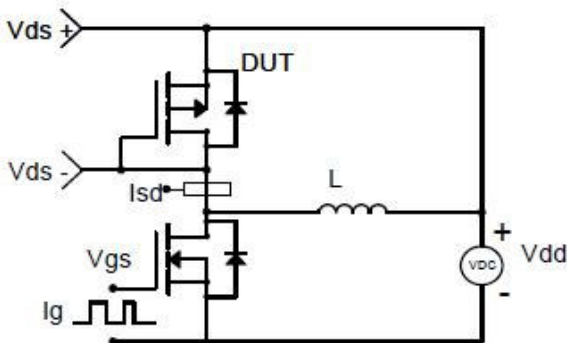
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

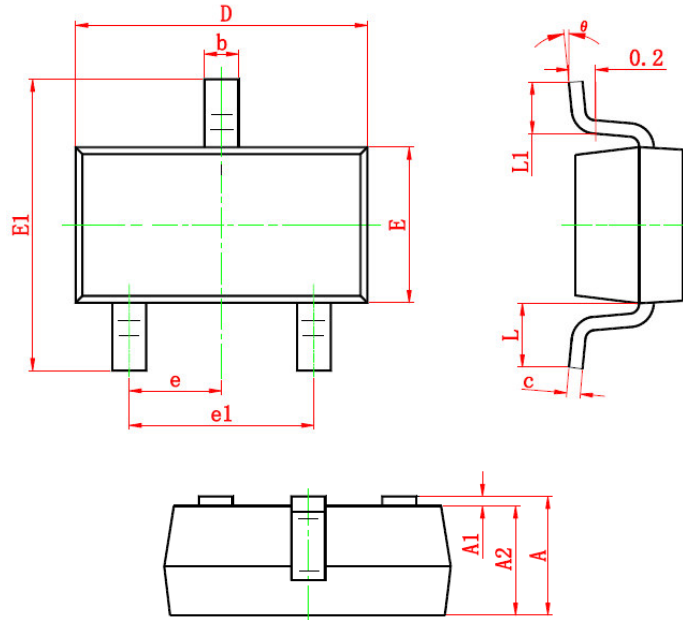


Diode Recovery Test Circuit & Waveforms





Package Information (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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